Franz J Tegude

List of Publications by Year
in descending order

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41	576	840776 11	610901 24
papers	citations	h-index	g-index

42	42	42	842
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Controllable p-type doping of GaAs nanowires during vapor-liquid-solid growth. Journal of Applied Physics, 2009, 105, .	2.5	104
2	High-Speed GaN/GaInN Nanowire Array Light-Emitting Diode on Silicon(111). Nano Letters, 2015, 15, 2318-2323.	9.1	103
3	n-Type Doping of Vaporâ€“Liquidâ€“Solid Grown GaAs Nanowires. Nanoscale Research Letters, 2011, 6, 65.	5.7	58
4	nâ€GaAs/InGaP/pâ€GaAs Coreâ€Multishell Nanowire Diodes for Efficient Lightâ€toâ€Current Conversion. Advanced Functional Materials, 2012, 22, 929-936.	14.9	56
5	Axial pn-junctions formed by MOVPE using DEZn and TESn in vaporâ€“liquidâ€“solid grown GaAs nanowires. Journal of Crystal Growth, 2011, 315, 143-147.	1.5	33
6	Optical properties of heavily doped GaAs nanowires and electroluminescent nanowire structures. Nanotechnology, 2011, 22, 085702.	2.6	29
7	High-Frequency Measurements on InAs Nanowire Field-Effect Transistors Using Coplanar Waveguide Contacts. IEEE Nanotechnology Magazine, 2010, 9, 432-437.	2.0	21
8	Planar-defect characteristics and cross-sections of ã€ˆ001ã€‰, ã€ˆ111ã€‰, and ã€ˆ112ã€‰ InAs nanowires. Journal of Applied Physics, 2011, 109, 114320.	2.5	21
9	Sub-Nanosecond Pulse Generation using Resonant Tunneling Diodes for Impulse Radio. , 2007, , .		19
10	Ohmic contacts to n-GaAs nanowires. Journal of Applied Physics, 2011, 110, .	2.5	19
11	Surface Recombination Mechanism in Graded-Base InGaAsâ€“InP HBTs. IEEE Transactions on Electron Devices, 2004, 51, 1044-1045.	3.0	18
12	Effects of (NH4)2S passivation on the performance of graded-base InGaAs/InP HBTs. Physica Status Solidi A, 2004, 201, 1017-1021.	1.7	11
13	High performance III/V RTD and PIN diode on a silicon (001) substrate. Applied Physics A: Materials Science and Processing, 2007, 87, 539-544.	2.3	11
14	Comparison of the passivation effects on self- and non-self-aligned InP/InGaAs/InP double heterostructure bipolar transistors by low-temperature deposited SiNx. Journal of Applied Physics, 2004, 96, 777-783.	2.5	9
15	Polarityâ€•and Siteâ€Controlled Metal Organic Vapor Phase Epitaxy of 3Dâ€GaN on Si(111). Physica Status Solidi (B): Basic Research, 2018, 255, 1700485.	1.5	8
16	Mask-less MOVPE of arrayed n-GaN nanowires on site- and polarity-controlled AlN/Si templates. CrystEngComm, 2019, 21, 7476-7488.	2.6	8
17	A systematic study of Ga- and N-polar GaN nanowireâ€“shell growth by metal organic vapor phase epitaxy. CrystEngComm, 2020, 22, 5522-5532.	2.6	7
18	Single InGaAs nanowhiskers characterized by analytical transmission electron microscopy. Phase Transitions, 2006, 79, 727-737.	1.3	6

#	Article	IF	Citations
19	Spatially controlled VLS epitaxy of gallium arsenide nanowires on gallium nitride layers. CrystEngComm, 2020, 22, 1239-1250.	2.6	5
20	Integrated InGaAs pin-diode on exactly oriented silicon (001) substrate suitable for 10 Gbit/s digital applications. Conference Proceedings - Lasers and Electro-Optics Society Annual Meeting-LEOS, 2007, , .	0.0	4
21	Characterisation of GaAs nanowhiskers grown on GaAs and Si substrates. , 0, , .		3
22	Electrical characterization and transport model of n-gallium nitride nanowires. Applied Physics Letters, 2015, 107, 082103.	3.3	3
23	nâ€Doped InGaP Nanowire Shells in GaAs/InGaP Coreâ€“Shell pâ€“n Junctions. Physica Status Solidi (B): Basic Research, 2020, 257, 1900358.	1.5	3
24	Tunnelingâ€Related Leakage Currents in Coaxial GaAs/InGaP Nanowire Heterojunction Bipolar Transistors. Physica Status Solidi (B): Basic Research, 2021, 258, 2000395.	1.5	3
25	Buffer optimization for INP-ON-SI [001] quasi-substrates. , 0, , .		2
26	High-speed InP-based resonant tunnelling diode on silicon substrate. , 0, , .		2
27	Low-Temperature DC and RF Measurement and Modelling of InGaAs-InAlAs Resonant Tunneling Diodes down to 15 K. , 2006, , .		2
28	Single n-InAs Nanowire MIS-Field-Effect Transistor: Experimental and Simulation Results. , 2007, , .		2
29	On the temporal behavior of dc and rf characteristics of InAs nanowire MISFET. , 2009, , .		2
30	Fabrication and Electrical Characterisation of n-InAs Single Nanowhisker Field-Effect Transistors. , 0, , .		1
31	Large-Signal Performance of Resonant Tunnelling Diodes in K-Band Oscillators. , 2008, , .		1
32	Toward Nanowire HBT: Reverse Current Reduction in Coaxial GaAs/InGaP n(i)p and n(i)pn Core-Multishell Nanowires. Physica Status Solidi (A) Applications and Materials Science, 2018, 216, 1800562.	1.8	1
33	Different approaches for integrating HBTs and EAMs. , 0, , .		0
34	Manufacturability and electrical characteristics of Si/SiGe interband tunnelling diodes. , 0, , .		0
35	Optimizing lateral HBT design by utilizing performance estimations. , 0, , .		0
36	Fabrication of transferred-substrate HBT with simple technology. , 0, , .		0

#	Article	IF	Citations
37	InP-HEMT-TIA with Differential Optical Input Using Vertical High Topology Pin-Diodes. Indium Phosphide and Related Materials Conference (IPRM), IEEE International Conference on, 2007, , .	0.0	0
38	Monostable-Bistable Threshold Logic Elements in a fully complementary optical receiver circuit for high frequency applications. , 2008, , .		0
39	Large-Signal Performance of Resonant Tunnelling Diodes in K-Band Oscillators. , 2008, , .		0
40	Wavelength-selective receiver for simultaneous λ=1.3 µm and λ=1.55 µm RF optical transmission. , 2009, , .		0
41	Germanium Template Assisted Integration of Gallium Arsenide Nanocrystals on Silicon: A Versatile Platform for Modern Optoelectronic Materials. Advanced Optical Materials, 2018, 6, 1701329.	7.3	0